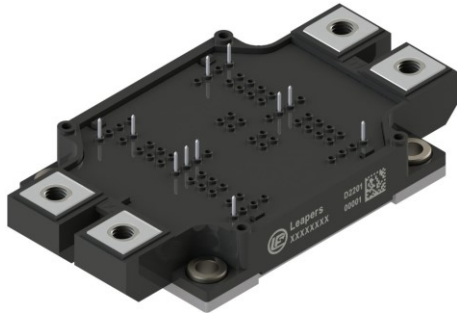


Description

The DFS500HF12I3C2 is a Half Bridge SiC MOSFET Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Motor drives and Renewable energy.



Features

- 1200V/4.3mΩ
- Low thermal resistance with Si₃N₄ AMB
- 175°C maximum junction temperature
- Low inductive design
- Thermistor inside
- Pressfit terminal
- Copper base size: 79mm*62mm

Applications

- xEV Applications
- Motor Drive
- Vehicle Fast Chargers
- Renewable energy

Circuit diagram

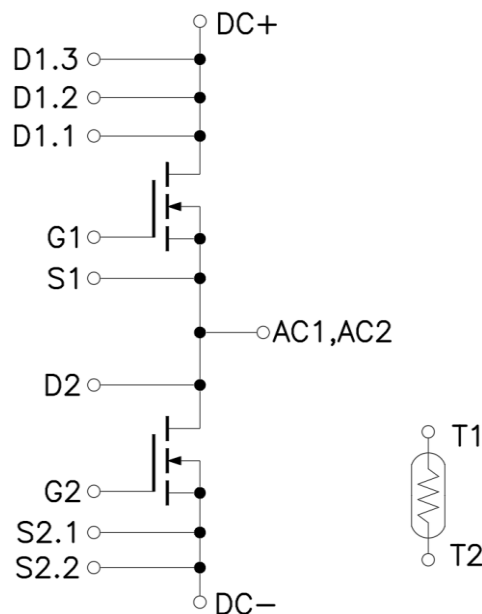


Figure 1. Out drawing & circuit diagram for DFS500HF12I3C2

Pin Configuration and Marking Information

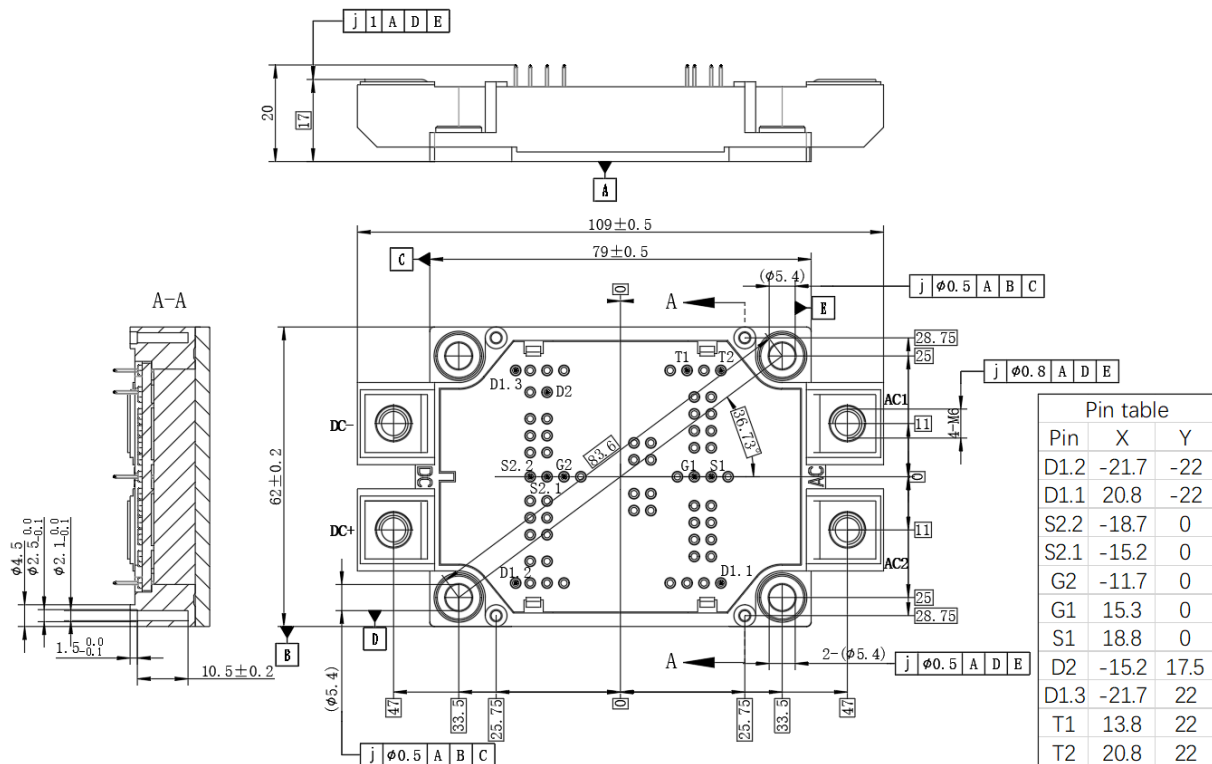


Figure 2. Pin configuration

Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, f =50Hz, t =1min	3.4	KV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	14.5 10	mm
Clearance	terminal to heatsink terminal to terminal	12.5 10	mm
CTI	-	>400	-
Module lead resistance, terminals – chip	T _C =25°C	0.3	mΩ
Mounting torque for module mounting	M5, M6	3 to 6	Nm
Weight	-	250	g

Maximum Ratings (T_j = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-Source Voltage	G-S Short	1200	V
V _{GSS}	Gate-Source Voltage	D-S Short, AC frequency ≥ 1Hz, Note1	-10 to 20	V
I _{DS}	DC Continuous Drain Current	T _f = 25°C, V _{GS} = +15V	530	A
I _{DS}	DC Continuous Drain Current	T _f = 65°C, V _{GS} = +15V	450	A
I _{SD}	Source (Body diode) Current	T _f = 25°C, with ON signal	530	A
I _{SD}	Source (Body diode) Current	T _f = 65°C, with ON signal	450	A
I _{DSM}	Pulse Drain Current	T _c = 65°C, Pulse width = 1ms, V _{GS} = +15V, Note2	1000	A
P _{tot}	Total Power Dissipation	T _c = 25°C	2140	W
T _{jmax}	Max Junction Temperature	-	175	°C
T _{stg}	Storage Temperature	-	-40 to 125	°C

Note1: Recommended Operating Value, +15V/-5V, +15V/-4V

Note2: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R ₂₅	Resistance	T _c = 25°C	-	5	-	kΩ
ΔR/R	Deviation of R100	T _c = 100°C, R ₁₀₀ = 493Ω	5	-	5	%
P ₂₅	Power dissipation	T _c = 25°C	-	-	20	mW
B _{25/50}	B-value	R ₂ = R ₂₅ exp [B _{25/50} (1/T ₂ - 1/(298,15 K))]	-	3375	-	K
B _{25/80}	B-value	R ₂ = R ₂₅ exp [B _{25/80} (1/T ₂ - 1/(298,15 K))]	-	3411	-	K
B _{25/100}	B-value	R ₂ = R ₂₅ exp [B _{25/100} (1/T ₂ - 1/(298,15 K))]	-	3433	-	K

MOSFET Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =500uA		1200	-	-	V
I _{DSS}	Zero gate voltage drain Current	V _{DS} =1200V, V _{GS} =0V		-	5	-	μA
V _{GS(th)}	Gate-source threshold Voltage	I _D =175mA, V _{DS} =V _{GS}	T _j =25°C	1.8	2.7	-	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V, V _{DS} =0V	T _j =25°C	-	-	500	nA
R _{DS(on)} (Chip)	Static drain-source	I _D =500A	T _j =25°C	-	4.3	5.8	mΩ
	On-state resistance	V _{GS} =+15V	T _j =175°C	-	6.2	-	mΩ
V _{DS(on)} (Chip)	Static drain-source	I _D =500A	T _j =25°C	-	2.15	2.90	V
	On-state Voltage	V _{GS} =+15V	T _j =175°C	-	3.10	-	V
C _{iss}	Input Capacitance	V _D =800V, V _{GS} =0V, f =100KHz		-	29.0	-	nF
C _{oss}	Output Capacitance			-	0.88	-	nF
C _{rss}	Reverse transfer Capacitance			-	0.072	-	nF
Q _g	Total gate charge	V _{DD} =800V, I _D =180A, V _{GS} =+15/-5V		-	540	-	nC
t _{d(on)}	Turn-on delay time	V _{DD} =600V I _D =500A V _{GS} =+15/-4V R _{gon} /R _{goff} =5.1/3.3Ω Inductive load switching operation	T _j =25°C	-	42	-	ns
			T _j =150°C	-	40	-	
t _r	Rise time		T _j =25°C	-	24	-	ns
			T _j =150°C	-	18	-	
t _{d(off)}	Turn-off delay time		T _j =25°C	-	111	-	ns
			T _j =150°C	-	119	-	
t _f	Fall time		T _j =25°C	-	14	-	ns
			T _j =150°C	-	39	-	
E _{on}	Turn-on power dissipation		T _j =25°C	-	20.5	-	mJ
			T _j =150°C	-	19.6	-	
E _{off}	Turn-off power dissipation		T _j =25°C	-	8.58	-	mJ
			T _j =150°C	-	9.41	-	
R _{th(j-c)}	FET Thermal Resistance	Junction to Case		-	0.07	-	K/W
R _{th(c-f)}	Contact thermal Resistance	With thermal conductive grease, Note3		-	0.015	-	K/W

Note3: Assumes Thermal Conductivity of grease is 0.9W/m·K and thickness is 50um.

Body Diode Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{SD}	Body Diode Forward Voltage	V _{GS} =-5V I _{SD} =500A	T _j =25°C	-	5.2	-	V
			T _j =175°C	-	4.3	-	
T _{rr}	Reverse recovery time	V _{DD} =600V I _D =500A	T _j =25°C	-	25	-	ns
			T _j =150°C	-	48	-	
Q _{rr}	Reverse recovery charge	V _{GS} =+15/-4V R _{gon} /R _{goff} =5.1/3.3Ω	T _j =25°C	-	1.85	-	μC
			T _j =150°C	-	7.83	-	
E _{rr}	Diode switching power dissipation	Inductive load switching operation	T _j =25°C	-	1.15	-	mJ
			T _j =150°C	-	3.17	-	

Test Conditions

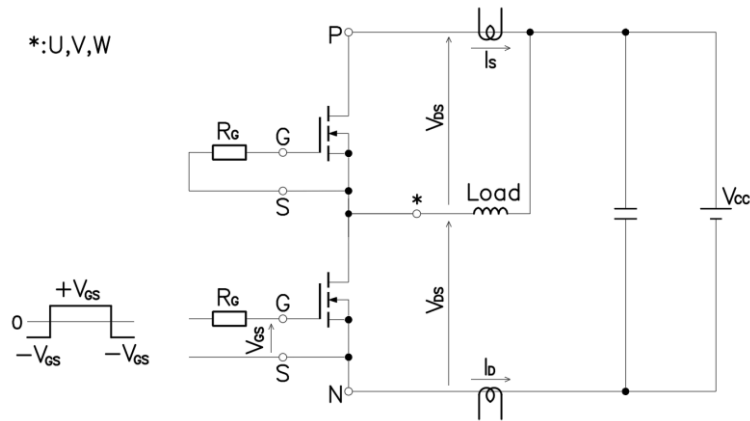


Figure 3. Switching time measure circuit

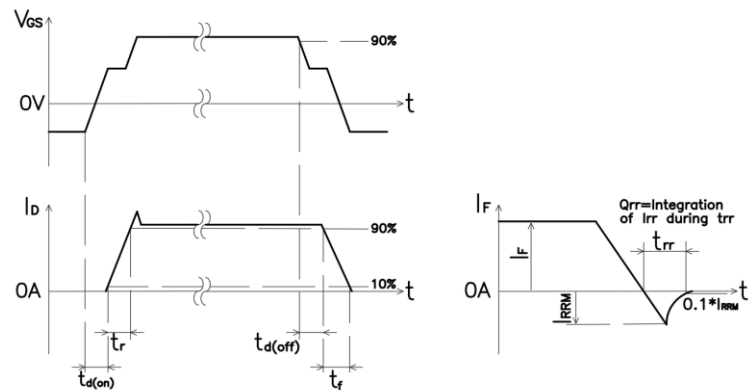


Figure 4. Switching time definition

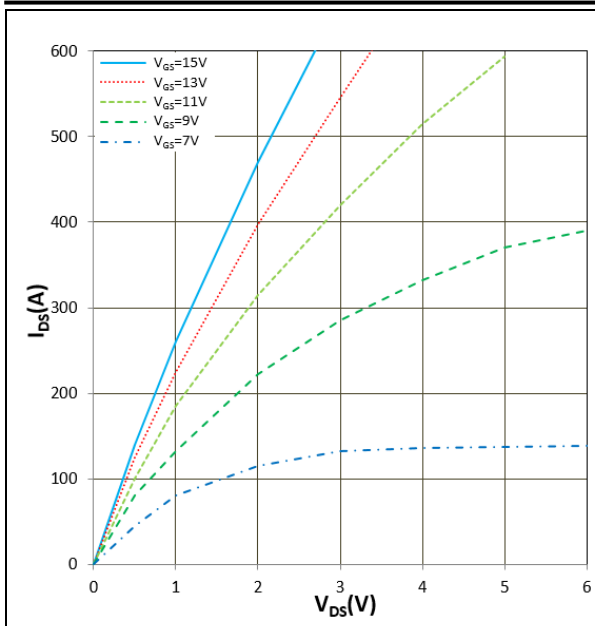


Figure 5. I_{DS} vs V_{DS}
 $T_j = 25^\circ\text{C}$

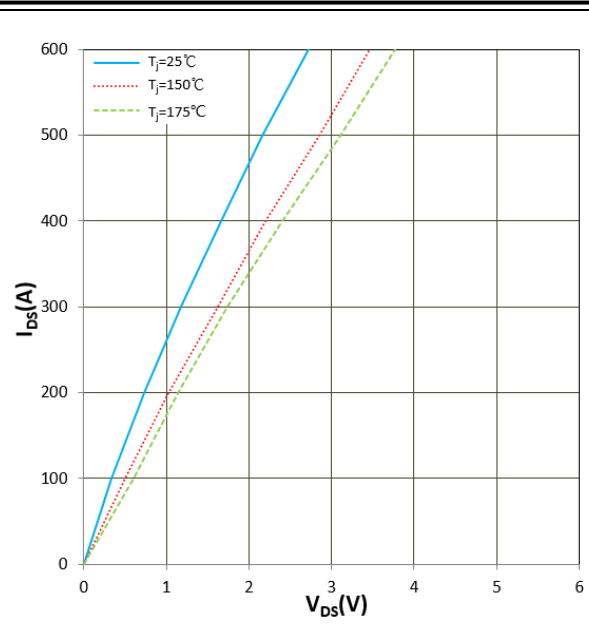


Figure 6. I_{DS} vs V_{DS}
 $V_{GS} = +15\text{V}$

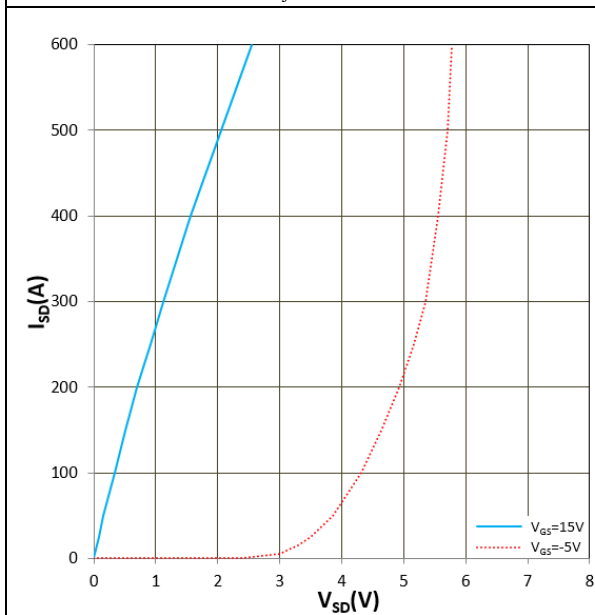


Figure 7. I_{SD} vs $V_{SD} (V_F)$
 $T_j = 25^\circ\text{C}$

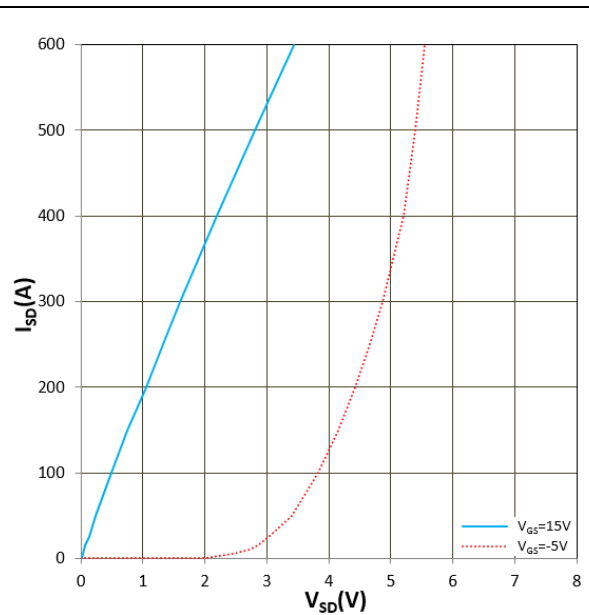


Figure 8. I_{SD} vs $V_{SD} (V_F)$
 $T_j = 175^\circ\text{C}$

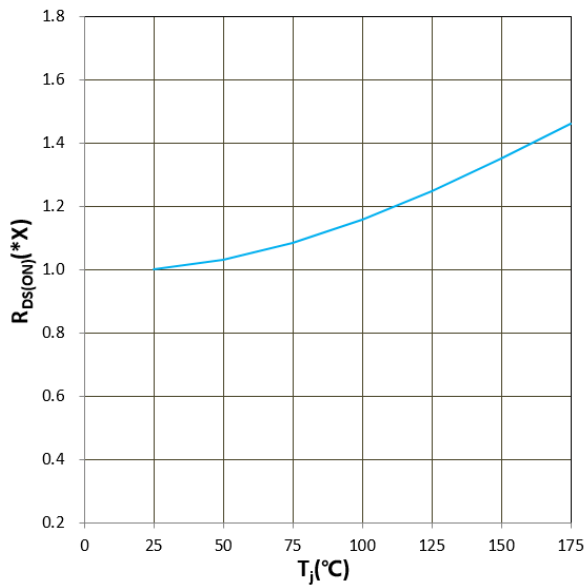


Figure 9. $R_{DS(on)}$ vs T_j
 $V_{GS} = +15V$, $I_D = 500A$, $1.0X = 4.3m\Omega$

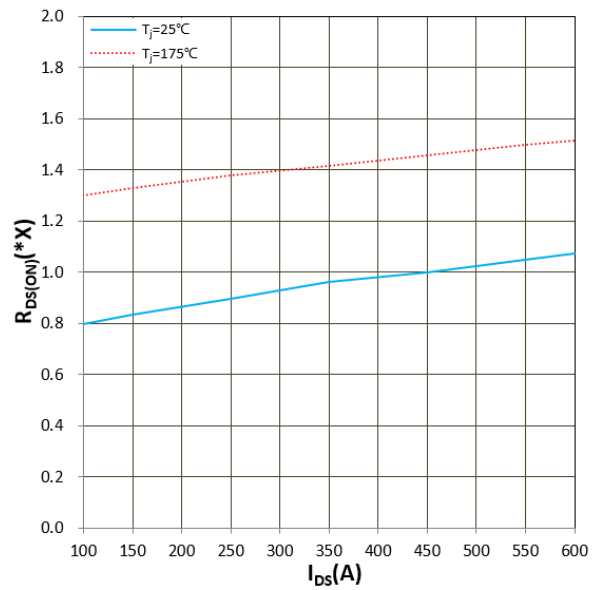


Figure 10. $R_{DS(on)}$ vs I_{DS}
 $V_{GS} = +15V$, $I_D = 500A$, $1.0X = 4.3m\Omega$

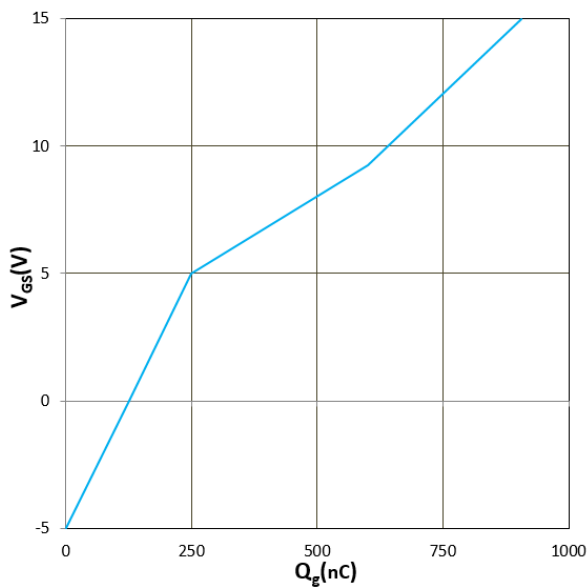


Figure 11. V_{GS} vs Q_g
 $V_{DS} = 800V$, $I_D = 300A$, $T_j = 25^\circ C$

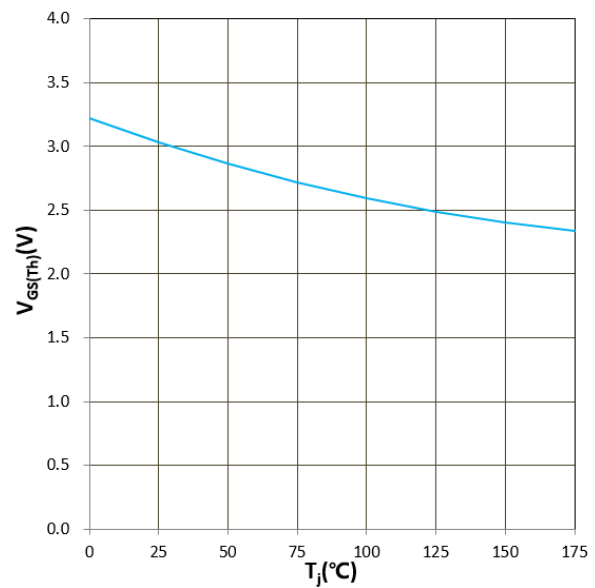


Figure 12. $V_{GS(th)}$ vs T_j
 $V_{GS} = V_{DS}$, $I_D = 175mA$

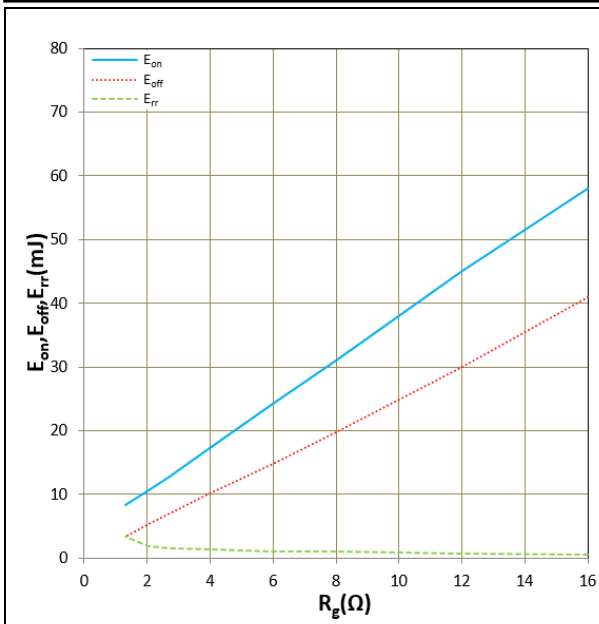


Figure 13. E_{on} , E_{off} , E_{rr} vs R_g
 $T_j = 25^\circ\text{C}$, $V_{CC} = 600\text{V}$, $V_{GS} = +15\text{V}/-4\text{V}$, $I_D = 500\text{A}$
 Inductive Load

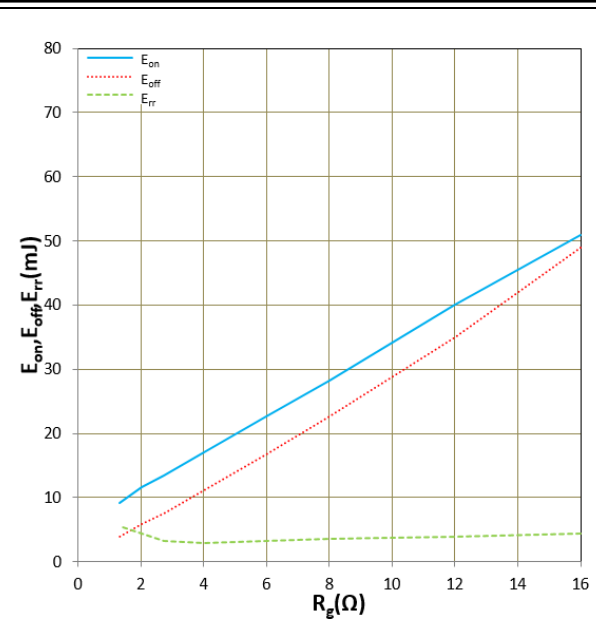


Figure 14. E_{on} , E_{off} , E_{rr} vs R_g
 $T_j = 150^\circ\text{C}$, $V_{CC} = 600\text{V}$, $V_{GS} = +15\text{V}/-4\text{V}$, $I_D = 500\text{A}$
 Inductive Load

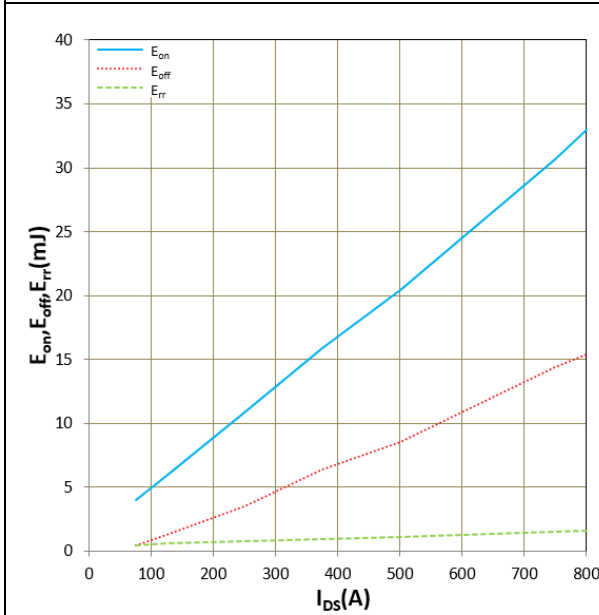


Figure 15. E_{on} , E_{off} , E_{rr} vs I_{DS}
 $T_j = 25^\circ\text{C}$, $V_{CC} = 600\text{V}$, $V_{GS} = +15\text{V}/-4\text{V}$
 $R_{gon}/R_{goff} = 5.1/3.3\Omega$, Inductive Load

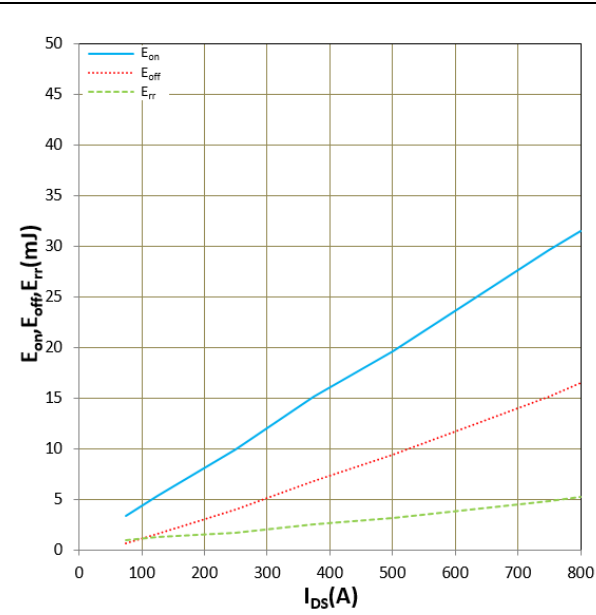


Figure 16. E_{on} , E_{off} , E_{rr} vs I_{DS}
 $T_j = 150^\circ\text{C}$, $V_{CC} = 600\text{V}$, $V_{GS} = +15\text{V}/-4\text{V}$
 $R_{gon}/R_{goff} = 5.1/3.3\Omega$, Inductive Load

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